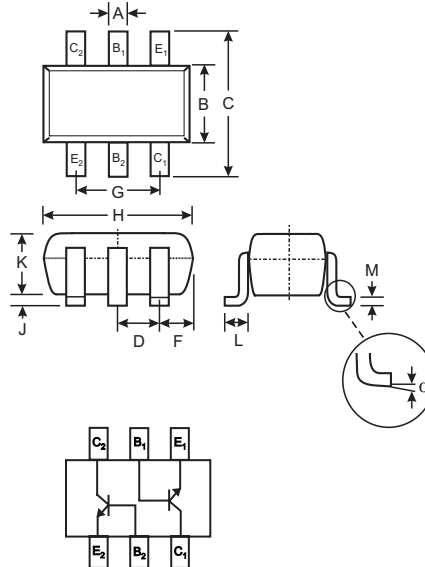


Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMDT5401)
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 3)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking (See Page 2): K4N
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I_C	200	mA
Power Dissipation (Note 1, 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Operating and Storage and Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. Maximum combined dissipation.
 3. No purposefully added lead.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

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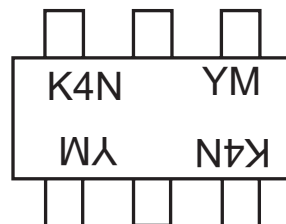
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	180	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	160	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CBO}	—	50	nA μA	$V_{CB} = 120\text{V}, I_E = 0$ $V_{CB} = 120\text{V}, I_E = 0, T_A = 100^\circ\text{C}$
Emitter Cutoff Current	I_{EBO}	—	50	nA	$V_{EB} = 4.0\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h_{FE}	80 80 30	— 250 —	—	$I_C = 1.0\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 5.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.15 0.20	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	1.0	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	6.0	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Small Signal Current Gain	h_{fe}	50	250	—	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA},$ $f = 1.0\text{kHz}$
Current Gain-Bandwidth Product	f_T	100	300	MHz	$V_{CE} = 10\text{V}, I_C = 10\text{mA},$ $f = 100\text{MHz}$
Noise Figure	NF	—	8.0	dB	$V_{CE} = 5.0\text{V}, I_C = 200\mu\text{A},$ $R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$

Ordering Information (Note 5)

Device	Packaging	Shipping
MMDT5551-7-F	SOT-363	3000/Tape & Reel

- Notes: 4. Short duration test pulse used to minimize self-heating effect.
5. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



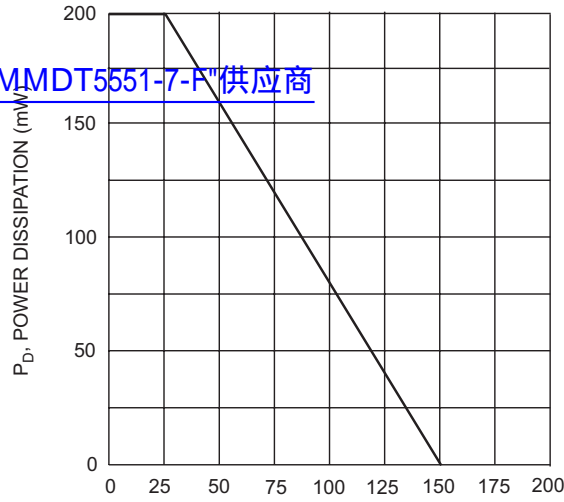
K4N = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

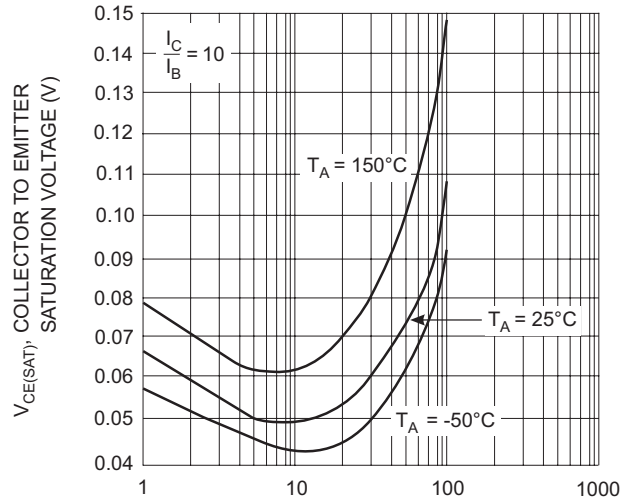
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

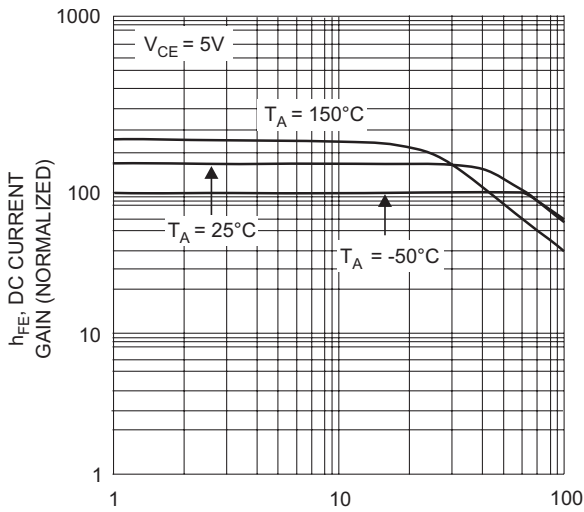
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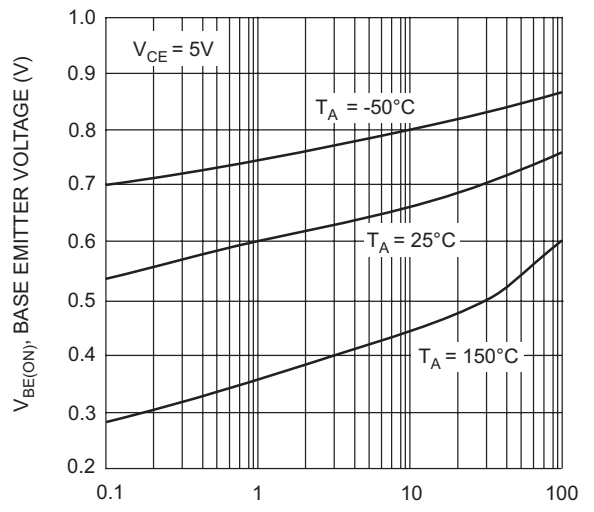
T_A , AMBIENT TEMPERATURE (°C)
Fig. 1, Max Power Dissipation vs Ambient Temperature



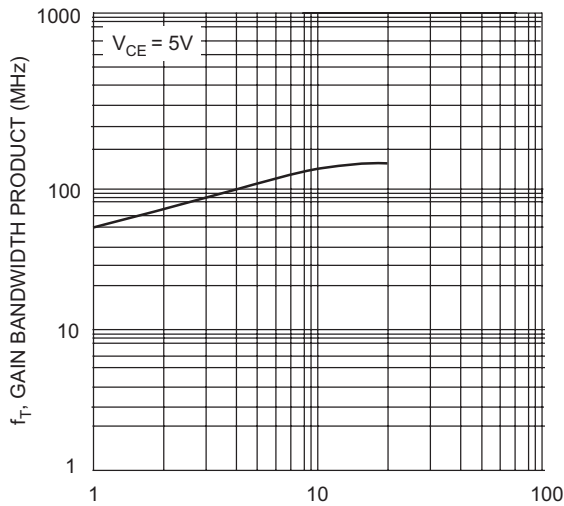
I_C , COLLECTOR CURRENT (mA)
Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 3, DC Current Gain vs Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 4, Base Emitter Voltage vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 5, Gain Bandwidth Product vs. Collector Current

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